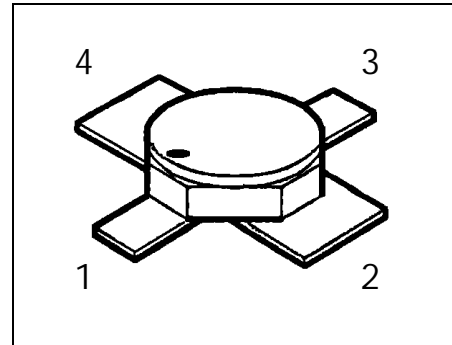


HiRel K-Band GaAs Super Low Noise HEMT

- **HiRel Discrete and Microwave Semiconductor**
- Conventional AlGaAs/GaAs HEMT
(For new design we recommend to use our pseudo-morphic HEMT CFY67)
- For professional super low-noise amplifiers
- For frequencies from 500 MHz to > 20 GHz
- Hermetically sealed microwave package
- Super low noise figure, high associated gain
-  **ESA Space Qualified**
ESA/SCC Detail Spec. No.: 5613/002,
Type Variant No.s 01 to 04



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Marking	Ordering Code	Pin Configuration				Package
			1	2	3	4	
CFY66-08 (ql)	-	see below	G	S	D	S	Micro-X
CFY66-08P (ql)							
CFY66-10 (ql)							
CFY66-10P (ql)							

CFY66-nnl: specifies gain and output power levels (see electrical characteristics)

(ql) Quality Level:	P: Professional Quality,	Ordering Code:	on request
	H: High Rel Quality,	Ordering Code:	on request
	S: Space Quality,	Ordering Code:	on request
	ES: ESA Space Quality,	Ordering Code:	on request

(see order instructions for ordering example)

Maximum Ratings

Parameter	Symbol	Values	Unit
Drain-source voltage	V_{DS}	3.5	V
Drain-gate voltage	V_{DG}	4.5	V
Gate-source voltage (reverse / forward)	V_{GS}	- 3... + 0.5	V
Drain current	I_D	60	mA
Gate forward current	I_G	2	mA
RF Input Power, C- and X-Band ¹⁾	$P_{RF,in}$	+ 10	dBm
Junction temperature	T_J	150	°C
Storage temperature range	T_{stg}	- 65... + 150	°C
Total power dissipation ²⁾	P_{tot}	200	mW
Soldering temperature ³⁾	T_{sol}	230	°C

Thermal Resistance

Junction-soldering point	R_{thJS}	≤ 515 (tbc.)	K/W
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Notes.:

- 1) For $V_{DS} \leq 2$ V. For $V_{DS} > 2$ V, derating is required.
- 2) At $T_S = + 47$ °C. For $T_S > + 47$ °C derating is required.
- 3) During 15 sec. maximum. The same terminal shall not be resoldered until 3 minutes have elapsed.

Electrical Characteristics (at $T_A=25^\circ\text{C}$; unless otherwise specified)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Drain-source saturation current $V_{DS} = 2\text{ V}, V_{GS} = 0\text{ V}$	I_{DSS}	10	30	60	mA
Gate threshold voltage $V_{DS} = 2\text{ V}, I_D = 1\text{ mA}$	$-V_{Gth}$	0.2	0.7	2.0	V
Drain current at pinch-off $V_{DS} = 1.5\text{ V}, V_{GS} = -3\text{ V}$	I_{Dp}	-	< 50	-	μA
Gate leakage current at pinch-off $V_{DS} = 1.5\text{ V}, V_{GS} = -3\text{ V}$	$-I_{Gp}$	-	< 50	200	μA
Transconductance $V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$	g_{m10}	40	55	-	mS
Gate leakage current at operation $V_{DS} = 2\text{ V}, I_D = 10\text{ mA}$	$-I_{G10}$	-	< 0.5	2	μA
Thermal resistance junction to soldering point	R_{thJS}	-	450	-	K/W

Electrical Characteristics (continued)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Noise figure ¹⁾ $V_{DS} = 2\text{ V}$, $I_D = 10\text{ mA}$, $f = 12\text{ GHz}$ CFY66-08, -08P CFY66-10, 10P	NF	-	0.7	0.8	dB
Associated gain. ¹⁾ $V_{DS} = 2\text{ V}$, $I_D = 10\text{ mA}$, $f = 12\text{ GHz}$ CFY66-08, -08P CFY66-10, 10P	G_a	10.0 9.5	11.0 10.5	- -	dB
Output power at 1 dB gain compression ²⁾ $V_{DS} = 2\text{ V}$, $I_D = 20\text{ mA}$, $f = 12\text{ GHz}$ CFY66-06, -08, -10 CFY66-08P, -10P	P_{1dB}	- 10.0	11.0 11.0	- -	dBm

Notes.:

1) Noise figure / associated gain characteristics given for minimum noise figure matching conditions (fixed generic matching, no fine-tuning).

2) Output power characteristics given for optimum output power matching conditions (fixed generic matching, no fine-tuning).

Typical Common Source S-Parameters

CFY66-08: $V_{DS} = 2\text{ V}$, $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$											
f	S11	<S11	S21	<S21	S12	<S12	S22	<S22	k-Fact.	S_{21}/S_{12}	MAG
[GHz]	[magn]	[angle]	[magn]	[angle]	[magn]	[angle]	[magn]	[angle]	[magn]	[dB]	[dB]
1,0	0,990	-21	4,451	161	0,0260	70	0,649	-16	0,14	22,3	
2,0	0,960	-39	4,282	144	0,0460	61	0,623	-29	0,19	19,7	
3,0	0,920	-57	4,148	126	0,0650	49	0,589	-43	0,27	18,0	
4,0	0,880	-77	3,979	108	0,0830	37	0,560	-57	0,32	16,8	
5,0	0,830	-95	3,727	93	0,0940	25	0,532	-70	0,39	16,0	
6,0	0,790	-111	3,444	78	0,1000	14	0,506	-83	0,47	15,4	
7,0	0,749	-124	3,206	64	0,1060	6	0,490	-94	0,55	14,8	
8,0	0,720	-137	3,029	50	0,1110	-3	0,463	-103	0,63	14,4	
9,0	0,690	-150	2,907	38	0,1130	-11	0,440	-113	0,70	14,1	
10,0	0,670	-165	2,845	25	0,1190	-20	0,420	-121	0,74	13,8	
11,0	0,649	179	2,787	11	0,1210	-28	0,400	-130	0,79	13,6	
12,0	0,628	164	2,699	-3	0,1200	-37	0,385	-143	0,84	13,5	
13,0	0,610	151	2,614	-16	0,1200	-46	0,370	-153	0,91	13,4	
14,0	0,597	138	2,584	-28	0,1190	-55	0,355	-162	0,96	13,4	
15,0	0,584	121	2,550	-42	0,1180	-66	0,340	-172	1,01	13,3	12,8
16,0	0,580	104	2,484	-56	0,1170	-76	0,330	178	1,05	13,3	11,9
17,0	0,580	89	2,461	-71	0,1150	-87	0,325	169	1,08	13,3	11,5
18,0	0,580	74	2,456	-86	0,1160	-100	0,320	160	1,09	13,3	11,4

Typical Common Source Noise-Parameters

CFY66-08: $V_{DS} = 2\text{ V}$, $I_D = 10\text{ mA}$, $Z_o = 50\ \Omega$				
f	$N_{F_{min}}$	$ \Gamma_{opt} $	$\angle\Gamma_{opt}$	R_n
[GHz]	[dB]	[magn]	[angle]	$[\Omega]$
1	0,27	0,770	16	17,85
2	0,31	0,720	30	16,55
3	0,35	0,672	43	15,27
4	0,38	0,634	57	13,75
5	0,42	0,604	71	11,99
6	0,46	0,578	85	10,04
7	0,50	0,558	100	8,15
8	0,55	0,541	114	6,30
9	0,60	0,528	128	4,74
10	0,65	0,517	143	3,45
11	0,70	0,506	157	2,58
12	0,74	0,496	171	2,16
13	0,79	0,485	-175	2,27
14	0,85	0,472	-160	2,88
15	0,89	0,457	-146	3,99
16	0,95	0,437	-132	5,59
17	1,00	0,415	-118	7,63
18	1,06	0,389	-102	9,96

Order Instructions:

Full type variant including quality level must be specified by the orderer. For *HiRel* Discrete and Microwave Semiconductors the ordering code specifies device family and quality level only.

Ordering Form:

Ordering Code: Q.....
CFY66 -(nml) (ql)
 -(nml) Noise Figure/Gain and/or Power Level
 (ql): Quality Level

Ordering Example:

Ordering Code: (on request)
CFY66-08P ES

For CFY66, Noise Figure/Gain/Power Level 08P:
 NF < 0.8 dB, G_a > 10.0 dB, P_{1dB} > 10 dBm @ 12 GHz
in ESA Space Quality Level

Further Informations:

See our WWW-Pages:

- Discrete and RF-Semiconductors (Small Signal Semiconductors)

www.infineon.com/products/discrete/hirel.htm

- *HiRel* Discrete and Microwave Semiconductors

www.infineon.com/products/discrete/hirel.htm

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Micro-X Package

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